

Sun Jin Yun

List of Publications by Year in descending order

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Version: 2024-02-01

56
papers

1,312
citations

361045

20
h-index

360668

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58
all docs

58
docs citations

58
times ranked

2273
citing authors

#	ARTICLE	IF	CITATIONS
1	Infrared spectroscopy and nano-imaging of the insulator-to-metal transition in vanadium dioxide. <i>Physical Review B</i> , 2009, 79, .	1.1	164
2	Dependence of atomic layer-deposited Al ₂ O ₃ films characteristics on growth temperature and Al precursors of Al(CH ₃) ₃ and AlCl ₃ . <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1997, 15, 2993-2997.	0.9	113
3	PEDOT:PSS Films with Greatly Enhanced Conductivity via Nitric Acid Treatment at Room Temperature and Their Application as Pt/TCO-Free Counter Electrodes in Dye-Sensitized Solar Cells. <i>Advanced Electronic Materials</i> , 2015, 1, 1500121.	2.6	96
4	Electrical Properties of Alumina Films by Plasma-Enhanced Atomic Layer Deposition. <i>Electrochemical and Solid-State Letters</i> , 2004, 7, F45.	2.2	93
5	Gate-Tunable Hole and Electron Carrier Transport in Atomically Thin Dual-Channel WSe ₂ /MoS ₂ Heterostructure for Ambipolar Field-Effect Transistors. <i>Advanced Materials</i> , 2016, 28, 9519-9525.	11.1	70
6	Comparison of trapped charges and hysteresis behavior in hBN encapsulated single MoS ₂ flake based field effect transistors on SiO ₂ and hBN substrates. <i>Nanotechnology</i> , 2018, 29, 335202.	1.3	70
7	High-yield graphene exfoliation using sodium dodecyl sulfate accompanied by alcohols as surface-tension-reducing agents in aqueous solution. <i>Carbon</i> , 2015, 83, 136-143.	5.4	52
8	Clean Interface Contact Using a ZnO Interlayer for Low-Contact-Resistance MoS ₂ Transistors. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 5031-5039.	4.0	50
9	Highly transparent amorphous silicon solar cells fabricated using thin absorber and high-bandgap-energy n/i-interface layers. <i>Solar Energy Materials and Solar Cells</i> , 2014, 128, 301-306.	3.0	40
10	Colored a-Si:H transparent solar cells employing ultrathin transparent multi-layered electrodes. <i>Solar Energy Materials and Solar Cells</i> , 2017, 163, 164-169.	3.0	40
11	Tunable electrical properties of multilayer HfSe ₂ field effect transistors by oxygen plasma treatment. <i>Nanoscale</i> , 2017, 9, 1645-1652.	2.8	38
12	Transparent Thin-Film Silicon Solar Cells for Indoor Light Harvesting with Conversion Efficiencies of 36% without Photodegradation. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 27122-27130.	4.0	36
13	Fabrication of CaS:Pb blue phosphor by incorporating dimeric Pb ²⁺ luminescent centers. <i>Applied Physics Letters</i> , 2001, 78, 721-723.	1.5	33
14	Bifacial color realization for a-Si:H solar cells using transparent multilayered electrodes. <i>Solar Energy</i> , 2018, 159, 465-474.	2.9	25
15	Observation of negative differential resistance in mesoscopic graphene oxide devices. <i>Scientific Reports</i> , 2018, 8, 7144.	1.6	25
16	VO_2 Thin-Film Varistor Based on Metal-Insulator Transition. <i>IEEE Electron Device Letters</i> , 2010, 31, 14-16.	2.2	22
17	Oxide-silicon-oxide buffer structure for ultralow temperature polycrystalline silicon thin-film transistor on plastic substrate. <i>IEEE Electron Device Letters</i> , 2006, 27, 579-581.	2.2	21
18	Low-voltage and high-gain pentacene inverters with plasma-enhanced atomic-layer-deposited gate dielectrics. <i>Applied Physics Letters</i> , 2006, 89, 033511.	1.5	21

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19	High-Performance Ultralow-Temperature Polycrystalline Silicon TFT Using Sequential Lateral Solidification. <i>IEEE Electron Device Letters</i> , 2004, 25, 550-552.	2.2	20
20	Gate Tunable Self-Biased Diode Based on Few Layered MoS ₂ and WSe ₂ . <i>Chemistry of Materials</i> , 2018, 30, 1011-1016.	3.2	20
21	Na ⁺ -Assisted Exfoliation of MX ₂ (M = Mo, W; X = S, Se) Nanosheets in an Aqueous Medium with the Aid of a Polymeric Surfactant for Flexible Polymer-Nanocomposite Memory Applications. <i>Small</i> , 2018, 14, 1702747.	5.2	19
22	Tunable Electron and Hole Injection Enabled by Atomically Thin Tunneling Layer for Improved Contact Resistance and Dual Channel Transport in MoS ₂ /WSe ₂ van der Waals Heterostructure. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 23961-23967.	4.0	17
23	Synthesis and gas sensing properties of WS ₂ nanocrystallites assembled hierarchical WS ₂ fibers by electrospinning. <i>Nanotechnology</i> , 2020, 31, 105602.	1.3	16
24	Insulators with High Stability for Electroluminescent Devices. <i>Japanese Journal of Applied Physics</i> , 2003, 42, L663-L665.	0.8	14
25	Photodetector Based on Multilayer SnSe ₂ Field Effect Transistor. <i>Journal of Nanoscience and Nanotechnology</i> , 2018, 18, 4243-4247.	0.9	14
26	Effective deicing of vehicle windows and thermal response of asymmetric multilayered transparent-film heaters. <i>Journal of Alloys and Compounds</i> , 2019, 774, 1092-1101.	2.8	14
27	CuO _x /a-Si:H heterojunction thin-film solar cell with an n-type a-Si:H depletion-assisting layer. <i>Progress in Photovoltaics: Research and Applications</i> , 2015, 23, 1642-1648.	4.4	12
28	Visible Light-Erasable Oxide FET-Based Nonvolatile Memory Operated with a Deep Trap Interface. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 26405-26412.	4.0	12
29	Polyvinylalcohol (PVA)-Assisted Exfoliation of ReS ₂ Nanosheets and the Use of ReS ₂ -PVA Composites for Transparent Memristive Photosynapse Devices. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 8919-8928.	4.0	12
30	Influence of a two-dimensional SiO ₂ nanorod structure on the extraction efficiency of ZnS:Mn thin-film electroluminescent devices. <i>Applied Physics Letters</i> , 2004, 84, 1377-1379.	1.5	10
31	Improved stability of electrical properties of nitrogen-added Al ₂ O ₃ films grown by PEALD as gate dielectric. <i>Materials Research Bulletin</i> , 2016, 83, 597-602.	2.7	10
32	Unimer-Assisted Exfoliation for Highly Concentrated Aqueous Dispersion Solutions of Single- and Few-Layered van der Waals Materials. <i>Langmuir</i> , 2017, 33, 1217-1226.	1.6	9
33	Improved adhesion of multi-layered front electrodes of transparent a-Si:H solar cells for varying front colors. <i>Solar Energy Materials and Solar Cells</i> , 2018, 183, 92-100.	3.0	9
34	Junctionless Diode Enabled by Self-Bias Effect of Ion Gel in Single-Layer MoS ₂ Device. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 26983-26989.	4.0	8
35	Metal-agglomeration-suppressed growth of MoS ₂ and MoSe ₂ films with small sulfur and selenium molecules for high mobility field effect transistor applications. <i>Nanoscale</i> , 2018, 10, 15213-15221.	2.8	8
36	Photoinduced Synaptic Behavior of In _x Ti _y O Thin Film Transistors. <i>Advanced Electronic Materials</i> , 2021, 7, 2001049.	2.6	8

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37	High performance self-gating graphene/MoS ₂ diode enabled by asymmetric contacts. Nanotechnology, 2018, 29, 395201.	1.3	7
38	Etching Characteristics of Manganese-Doped Zinc Sulfide Film Using Cl ₂ /CF ₄ Inductively Coupled Plasma. Japanese Journal of Applied Physics, 2004, 43, 2716-2720.	0.8	6
39	Threshold voltage control of pentacene thin-film transistor with dual-gate structure. Journal of Information Display, 2006, 7, 27-30.	2.1	6
40	Scattering Matrix Analysis for Evaluating the Photocurrent in Hydrogenated-Amorphous-Silicon-Based Thin Film Solar Cells. Journal of Nanoscience and Nanotechnology, 2014, 14, 8309-8314.	0.9	6
41	Arbitrary alignment-angle control method of electrospun fibers: potential for a stretchable electrode material. RSC Advances, 2017, 7, 44945-44953.	1.7	6
42	Photo-Carrier-Guiding Behavior of Vertically Grown MoS ₂ and MoSe ₂ in Highly Efficient Low-Light Transparent Photovoltaic Devices on Large-Area Rough Substrates. ACS Applied Materials & Interfaces, 2020, 12, 1368-1377.	4.0	6
43	Multi-Level Long-Term Memory Resembling Human Memory Based on Photosensitive Field-Effect Transistors with Stable Interfacial Deep Traps. Advanced Electronic Materials, 2020, 6, 1901044.	2.6	6
44	Cell performance of a-Si:H translucent solar cells with various buffers utilizing light reflected by a backside mirror. Materials Research Bulletin, 2014, 58, 153-156.	2.7	5
45	Studies on Microvoids at the Interface of Direct Bonded Silicon Wafers. Journal of the Electrochemical Society, 1992, 139, 2326-2330.	1.3	4
46	P-56: Blue-Emitting dc CaS:Pb Electroluminescent Device. Digest of Technical Papers SID International Symposium, 2001, 32, 763.	0.1	4
47	Self-aligned Thin Film Transistor Fabrication with an Ultra Low Temperature Polycrystalline Silicon Process on a Benzocyclobutene Planarized Stainless Steel Foil Substrate. Materials Research Society Symposia Proceedings, 2006, 910, 3.	0.1	3
48	Etching Characteristics and Mechanisms of TiO ₂ Thin Films in HBr/Ar and Cl ₂ /Ar Inductively-Coupled Plasmas. Plasma Chemistry and Plasma Processing, 2012, 32, 333-342.	1.1	3
49	Phase transition of hydrogenated SiGe thin films in plasma-enhanced chemical vapor deposition. Thin Solid Films, 2013, 546, 362-366.	0.8	3
50	The Characterization of Al ₂ O ₃ Films Grown by Atomic Layer Deposition Using Al(CH ₃) ₃ and H ₂ O. Materials Research Society Symposia Proceedings, 1997, 471, 81.	0.1	2
51	P-33: Effect of Rapid Thermal Annealing on CaS:Pb Electroluminescent Devices Containing Ta ₂ O ₅ as Insulating Layer. Digest of Technical Papers SID International Symposium, 2000, 31, 652-655.	0.1	1
52	P-31: Effect of Metal Surface Treatments on the Characteristics of MIM Diode for the FED Application. Digest of Technical Papers SID International Symposium, 2003, 34, 316.	0.1	0
53	Pentacene Organic Thin-Film Transistors with Dual-Gate Structure. Solid State Phenomena, 2007, 124-126, 383-386.	0.3	0
54	Improvement of c-Si surface passivation using dual intrinsic a-Si:H layers for silicon heterojunction solar cells. , 2013, , .		0

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55	Multi-wafer-scale growth of WSe ₂ films using a traveling flow-type reactor with a remote thermal Se cracker. Applied Surface Science, 2020, 528, 146951.	3.1	0
56	Characteristics of nanocomposite ZrO ₂ /Al ₂ O ₃ films deposited by plasma-enhanced atomic layer deposition. Journal of Nanoscience and Nanotechnology, 2007, 7, 4180-4.	0.9	0